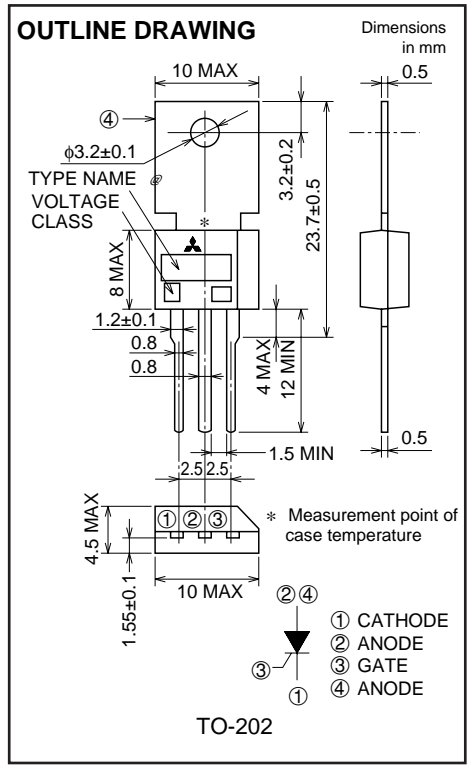
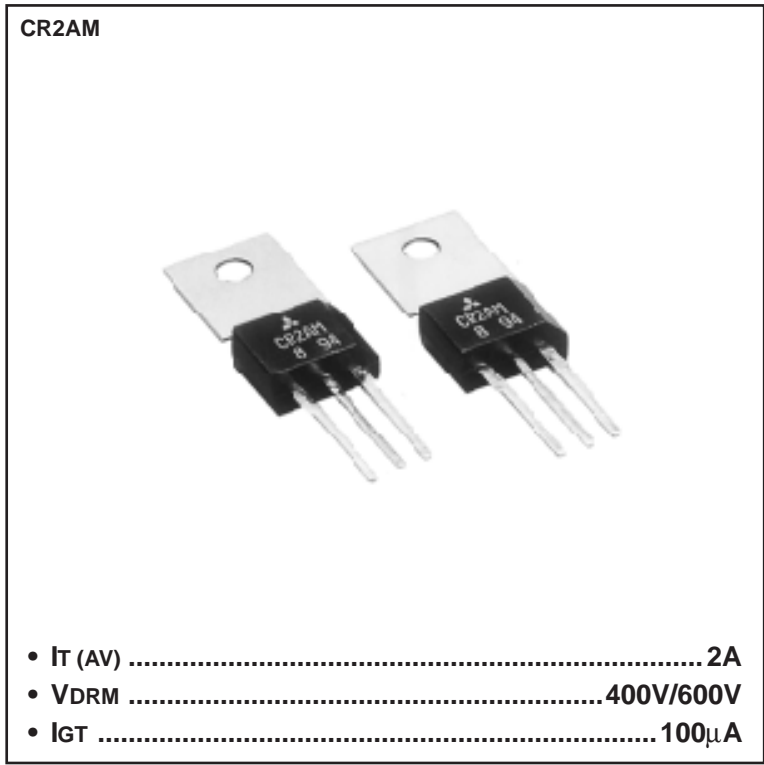


CR2AM

LOW POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE



APPLICATION

Control of household equipment such as electric blankets, leakage protector, static switch, other general purpose control applications, ignitors

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
V_{RRM}	Repetitive peak reverse voltage	400	600	V
V_{RSM}	Non-repetitive peak reverse voltage	500	720	V
V_R (DC)	DC reverse voltage	320	480	V
V_{DRM}	Repetitive peak off-state voltage *1	400	600	V
V_D (DC)	DC off-state voltage *1	320	480	V

Symbol	Parameter	Conditions	Ratings	Unit
I_T (RMS)	RMS on-state current		3.15	A
I_T (AV)	Average on-state current	Commercial frequency, sine half wave, 180° conduction, $T_c=75^\circ\text{C}$	2.0	A
I_{TSM}	Surge on-state current	60Hz sine half wave 1 full cycle, peak value, non-repetitive	20	A
I^2_t	I^2_t for fusing	Value corresponding to 1 cycle of half wave 60Hz, Surge on-state current	1.6	A^2s
PGM	Peak gate power dissipation		0.5	W
PG (AV)	Average gate power dissipation		0.1	W
V_{FGM}	Peak gate forward voltage		6	V
V_{RGM}	Peak gate reverse voltage		6	V
I_{FGM}	Peak gate forward current		0.3	A
T_j	Junction temperature		-40 ~ +125	$^\circ\text{C}$
T_{stg}	Storage temperature		-40 ~ +125	$^\circ\text{C}$
—	Weight	Typical value	1.6	g

*1. With Gate-to-cathode resistance $R_{GK}=1\text{k}\Omega$

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	$T_j=125^\circ\text{C}$, V_{RRM} applied	—	—	0.1	mA
IDRM	Repetitive peak off-state current	$T_j=125^\circ\text{C}$, V_{DRM} applied, $R_{GK}=1\text{k}\Omega$	—	—	0.1	mA
V_{TM}	On-state voltage	$T_c=25^\circ\text{C}$, $I_{TM}=4\text{A}$, Instantaneous value	—	—	1.8	V
V_{GT}	Gate trigger voltage	$T_j=25^\circ\text{C}$, $V_D=6\text{V}$, $I_T=0.1\text{A}$	—	—	0.8	V
V_{GD}	Gate non-trigger voltage	$T_j=125^\circ\text{C}$, $V_D=1/2V_{DRM}$, $R_{GK}=1\text{k}\Omega$	0.2	—	—	V
I_{GT}	Gate trigger current	$T_j=25^\circ\text{C}$, $V_D=6\text{V}$, $I_T=0.1\text{A}$	1	—	100*3	μA
$R_{th(j-c)}$	Thermal resistance	Junction to case *2	—	—	10	$^\circ\text{C/W}$

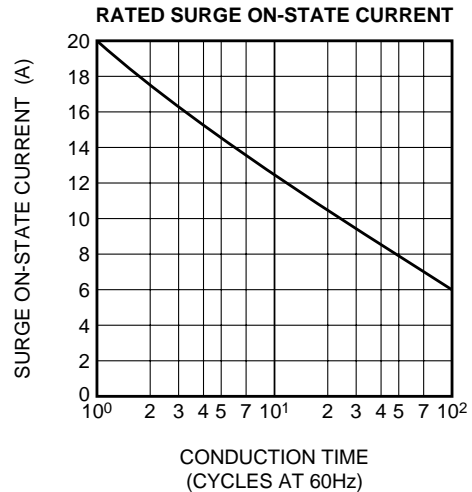
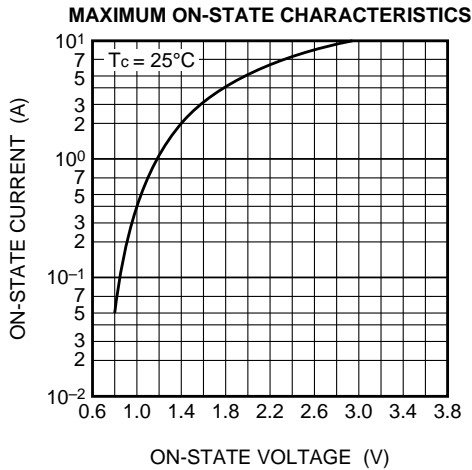
*2. The method point for case temperature is at the anode tab 1.5mm away from the molded case.

*3. If special values of I_{GT} are required, choose at least two items from those listed in the table below. (Example: AB, BC)

Item	A	B	C
I_{GT} (μA)	1 ~ 30	20 ~ 50	40 ~ 100

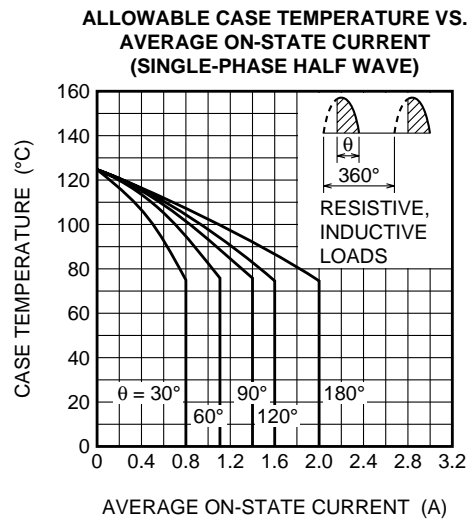
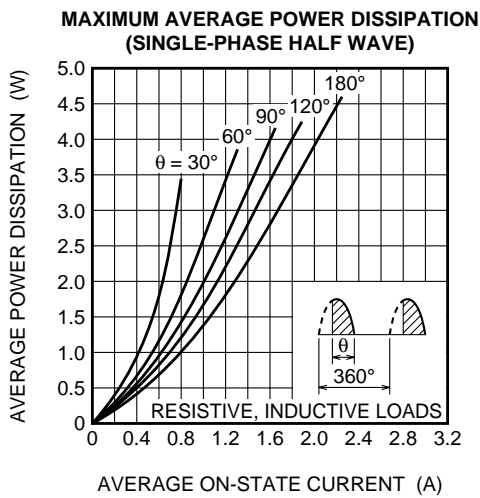
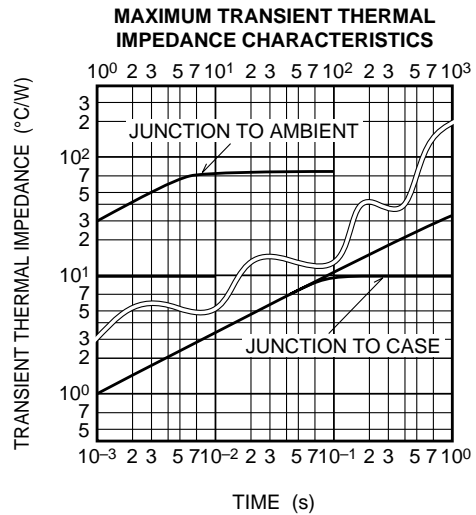
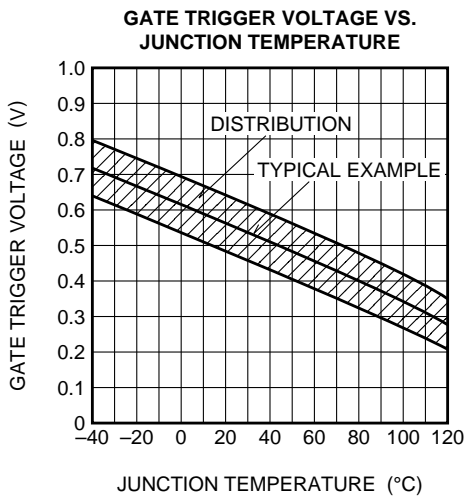
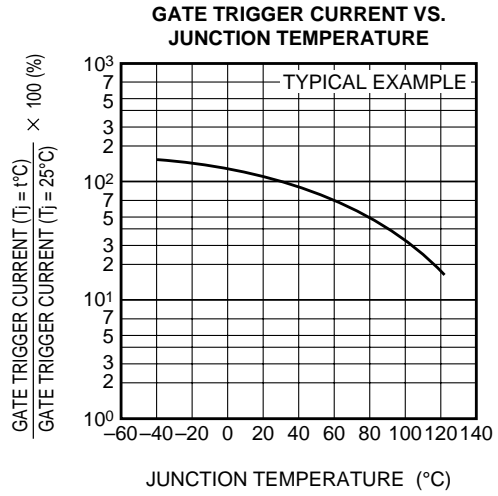
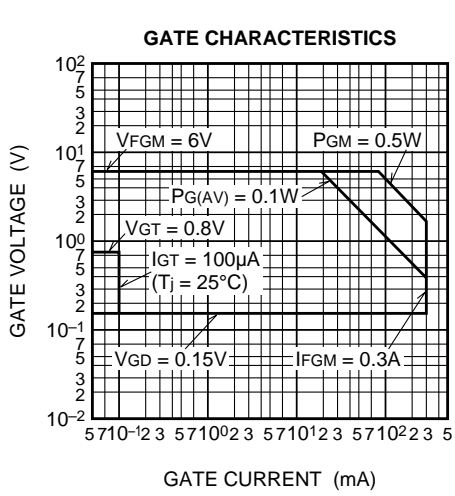
The above values do not include the current flowing through the $1\text{k}\Omega$ resistance between the gate and cathode.

PERFORMANCE CURVES



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LOW POWER USE
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

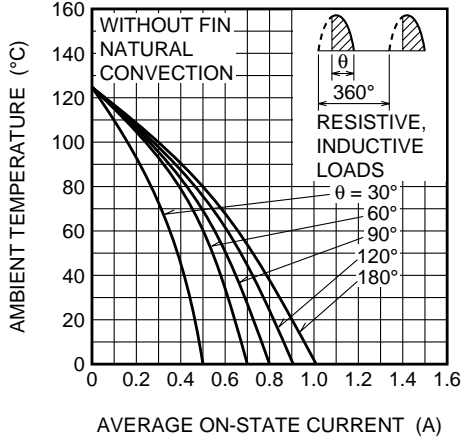


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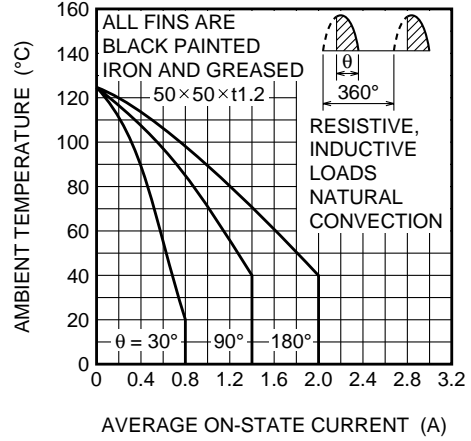
LOW POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE

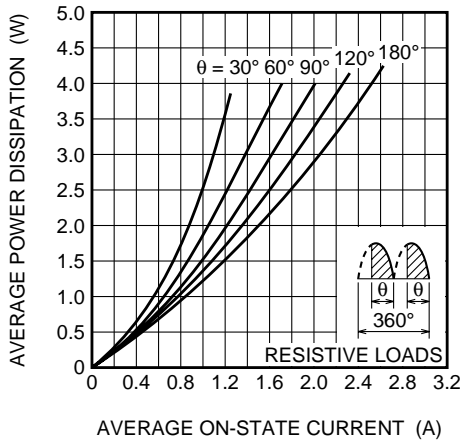
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



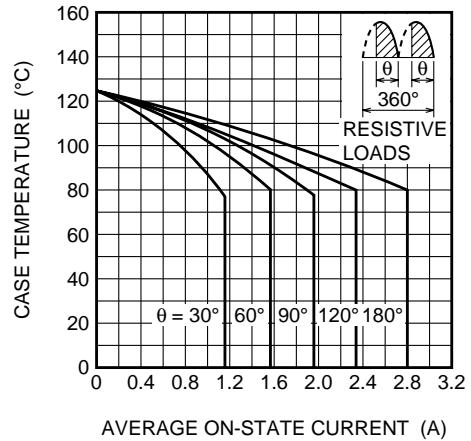
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



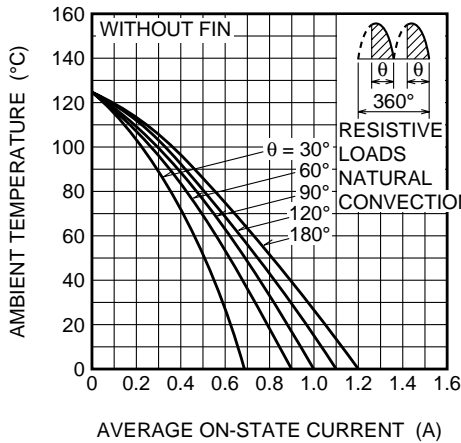
MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE FULL WAVE)



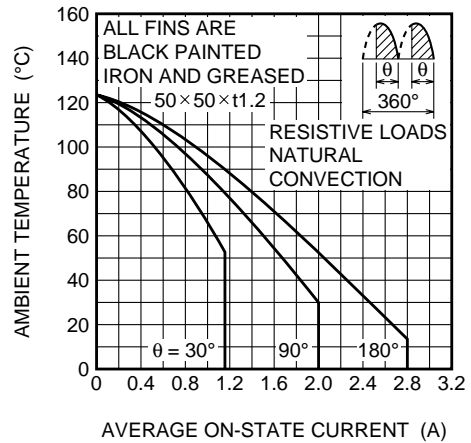
ALLOWABLE CASE TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)



ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)



ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)

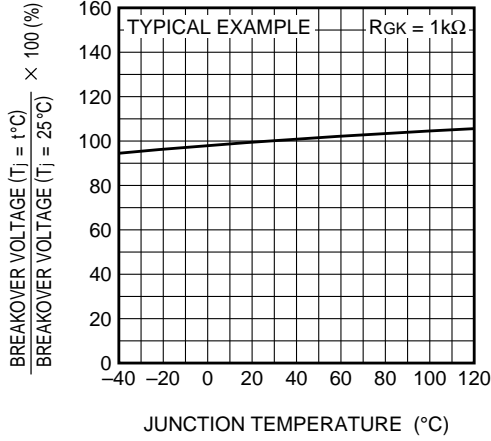


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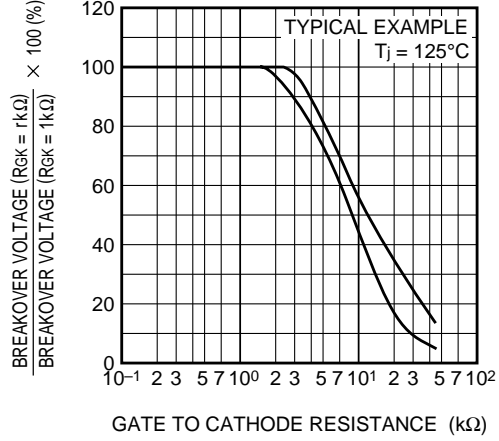
LOW POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE

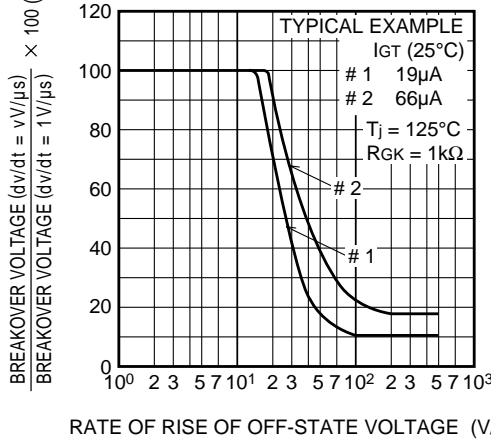
BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE



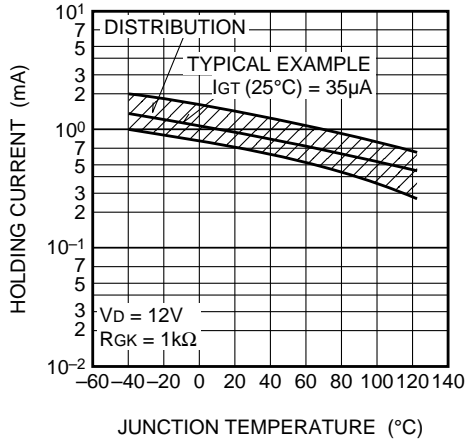
BREAKOVER VOLTAGE VS. GATE TO CATHODE RESISTANCE



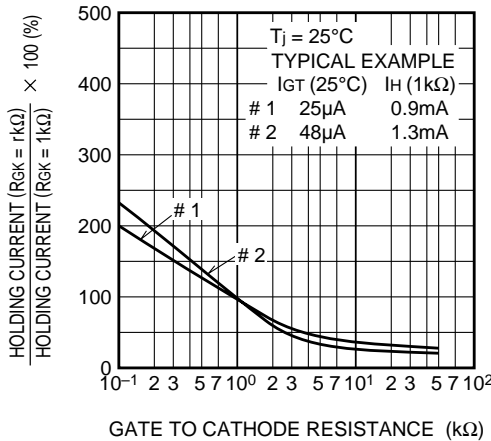
BREAKOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE



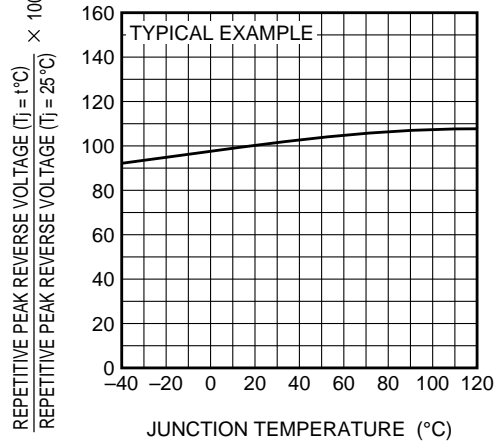
HOLDING CURRENT VS. JUNCTION TEMPERATURE



HOLDING CURRENT VS. GATE TO CATHODE RESISTANCE



REPETITIVE PEAK REVERSE VOLTAGE VS. JUNCTION TEMPERATURE



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LOW POWER USE
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

